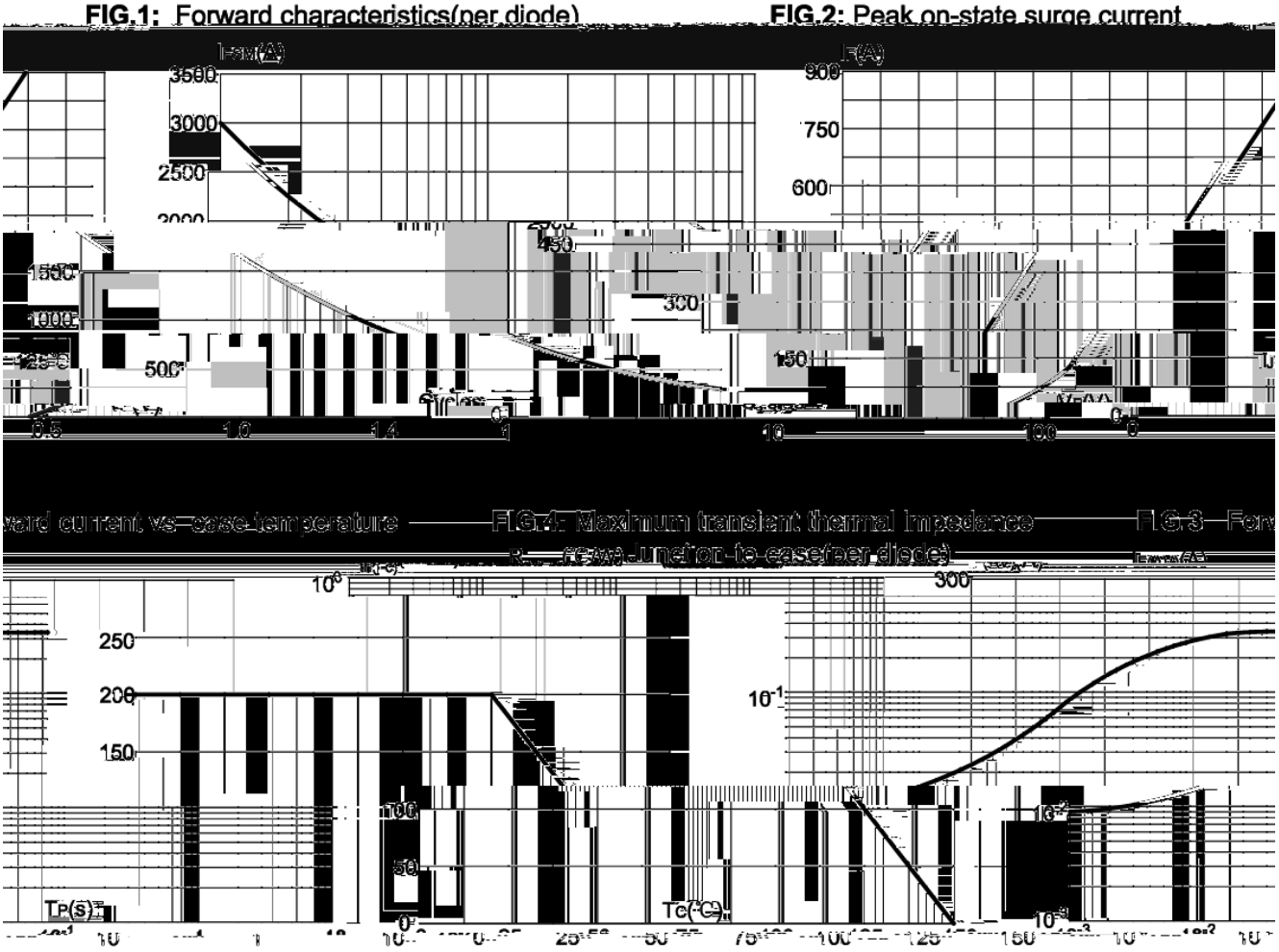
E Ch a (@ C = 25)

n	Ch	n				
			M	p	M	
g	I_F = 200A, T_{jv} = 25	V_F		0.85	0.90	V
	I_F = 200A, T_{jv} = 125			0.75	0.80	
M g	$V_R = V_{RM}$, T_{vj} = 25	I_{RM}			0.5	A

FIG.1: Forward characteristics(per diode)



ward current vs case temperature

FIG.4: Maximum transient thermal impedance

K/W—Transient thermal impedance—junction-to-case(per diode)

FIG.3—For

C

